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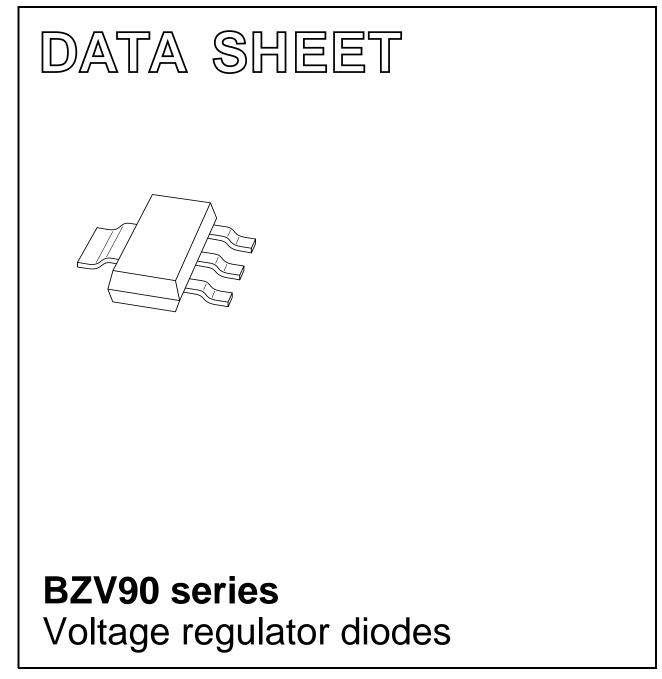
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Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1996 Oct 25



BZV90 series

FEATURES

- Total power dissipation: max. 1500 mW
- Tolerance series: approx. ±5%
- Working voltage range: nom. 2.4 to 75 V (E24 range)
- Non-repetitive peak reverse power dissipation: max. 40 W.

APPLICATIONS

• General regulation functions.

DESCRIPTION

Medium-power voltage regulator diodes in SOT223 plastic SMD packages.

The diodes are available in the normalized E24 approx. $\pm 5\%$ tolerance range. The series consists of 37 types with nominal working voltages from 2.4 to 75 V (BZV90-C2V4 to C75).

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _F	continuous forward current		-	400	mA
I _{ZSM}	non-repetitive peak reverse current	t _p = 100 μs; square wave; T _j = 25 °C prior to surge	see Table "Per type		
P _{tot}	total power dissipation	T _{amb} = 25 °C; note 1	-	1500	mW
P _{ZSM}	non-repetitive peak reverse power dissipation	t_p = 100 µs; square wave; T _j = 25 °C prior to surge; see Fig.2	_	40	W
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C

Note

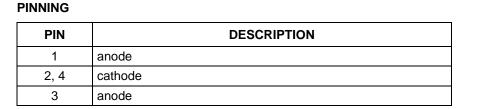
1. Device mounted on an FR4 double-sided copper-clad printed circuit-board; copper area = 2 cm².

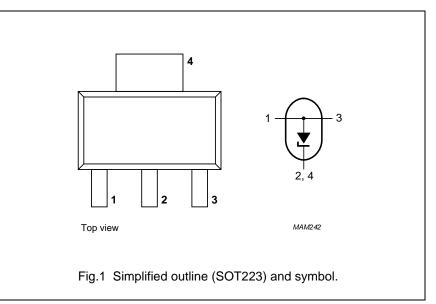
ELECTRICAL CHARACTERISTICS

Total series

 $T_i = 25 \ ^{\circ}C$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _F	forward voltage	I _F = 50 mA; see Fig.3	-	1.0	V





Per type T _j = 25 °C) unless	otherwise	Per type $T_j = 25 \circ C$ unless otherwise specified.									
BZV90- CXXX	WORKIN VOLTAG V _Z (V) at I _{Ztest}	WORKING VOLTAGE V _Z (V) at I _{Ztest}	DIFFERENTI RESISTANC r _{dif} (Ω) at I _{Ztest}	DIFFERENTIAL RESISTANCE r _{dif} (Ω) at I _{Ztest}	TEM See F	TEMP. COEFF. S _Z (mV/K) at I _{2test} see Figs 4 and 5	EFF. () nd 5	TEST CURRENT I _{Ztest} (mA)	DIODE CAP. C_d (pF) at f = 1 MHz; at V _R = 0 V	REVERSE CURRENT at REVERSE VOLTAGE	SE VT at SE GE	NON-REPETITIVE PEAK REVERSE CURRENT I _{2SM} (A) at t _p = 100 µs;
										I _R (ખ્ર)	V_R	T _{amb} = 25 °C
	MIN.	MAX.	TYP.	MAX.	MIN.	TYP.	MAX.		.XAM	MAX.	S	MAX.
2V4	2.2	2.6	70	100	-3.5	-1.6	0	5	450	50	1.0	6.0
2V7	2.5	2.9	75	100	-3.5	-2.0	0	5	450	20	1.0	6.0
3V0	2.8	3.2	80	95	-3.5	-2.1	0	5	450	10	1.0	6.0
3V3	3.1	3.5	85	95	-3.5	-2.4	0	5	450	5	1.0	6.0
3V6	3.4	3.8	85	06	-3.5	-2.4	0	5	450	5	1.0	6.0
3V9	3.7	4.1	85	06	-3.5	-2.5	0	5	450	3	1.0	6.0
4V3	4.0	4.6	80	06	-3.5	-2.5	0	5	450	3	1.0	6.0
4V7	4.4	5.0	50	80	-3.5	-1.4	0.2	5	300	3	2.0	6.0
5V1	4.8	5.4	40	60	-2.7	-0.8	1.2	5	300	2	2.0	6.0
5V6	5.2	6.0	15	40	-2.0	1.2	2.5	5	300	1	2.0	6.0
6V2	5.8	6.6	9	10	0.4	2.3	3.7	5	200	3	4.0	6.0
6V8	6.4	7.2	9	15	1.2	3.0	4.5	5	200	2	4.0	6.0
7V5	7.0	7.9	9	15	2.5	4.0	5.3	5	150	1	5.0	4.0
8V2	7.7	8.7	6	15	3.2	4.6	6.2	5	150	0.7	5.0	4.0
9V1	8.5	9.6	6	15	3.8	5.5	7.0	5	150	0.5	6.0	3.0
10	9.4	10.6	8	20	4.5	6.4	8.0	5	90	0.2	7.0	3.0
11	10.4	11.6	10	20	5.4	7.4	9.0	5	85	0.1	8.0	2.5
12	11.4	12.7	10	25	6.0	8.4	10.0	5	85	0.1	8.0	2.5
13	12.4	14.1	10	30	7.0	9.4	11.0	5	80	0.1	8.0	2.5
15	13.8	15.6	10	30	9.2	11.4	13.0	5	75	0.05	10.5	2.0
16	15.3	17.1	10	40	10.4	12.4	14.0	5	75	0.05	11.2	1.5
18	16.8	19.1	10	45	12.4	14.4	16.0	5	70	0.05	12.6	1.5
20	18.8	21.2	15	55	14.4	16.4	18.0	5	60	0.05	14.0	1.5

Voltage regulator diodes

1999 May 17

BZV90 series

NON-REPETITIVE PEAK REVERSE CURRENT I _{ZSM} (A) at t _p = 100 µs;	T _{amb} = 25 °C	MAX.	10	10											10	
NON-RE REVER at t	Tar		1.25	1.25	1.0	1.0	0.9	8.0	0.7	0.6	0.5	0.4	0.3	0.3	0.25	с U
tse VT at tse Ge	٧ _R	S	15.4	16.8	18.9	21.0	23.1	25.2	27.3	30.1	32.9	35.7	39.2	43.4	47.6	50 E
REVERSE CURRENT at REVERSE VOLTAGE	I _R (μA)	MAX.	0.05	0.05	0.05	0.05	0.05	0.05	0.05	0.05	0.05	0.05	0.05	0.05	0.05	0.05
DIODE CAP. C_d (pF) at f = 1 MHz; at V _R = 0 V		MAX.	60	55	50	50	45	45	45	40	40	40	40	35	35	35
TEST CURRENT I _{Ztest} (mA)			5	5	2	2	2	2	2	2	2	2	2	2	2	ç
EFF. () Ind 5		MAX.	20.0	22.0	25.3	29.4	33.4	37.4	41.2	46.6	51.8	57.2	63.8	71.6	79.8	200
TEMP. COEFF. S _Z (mV/K) at I _{2test} see Figs 4 and 5		ТҮР.	18.4	20.4	23.4	26.6	29.7	33.0	36.4	41.2	46.1	51.0	57.0	64.4	71.7	с U8
TEN S see		MIN	16.4	18.4	21.4	24.4	27.4	30.4	33.4	37.6	42.0	46.6	52.2	58.8	65.6	73.1
JIFFERENTIAL RESISTANCE r _{dif} (Ω) at I _{Ztest}		MAX.	55	20	80	80	80	06	130	150	170	180	200	215	240	755
DIFFERENTI RESISTANC r _{dif} (Ω) at I _{Ztest}		TYP.	20	25	25	30	35	35	40	45	50	60	70	80	06	05
KING AGE (V) trest		MAX.	23.3	25.6	28.9	32.0	35.0	38.0	41.0	46.0	50.0	54.0	60.0	66.0	72.0	70.0
WORKING VOLTAGE V _Z (V) at I _{Ztest}		MIN.	20.8	22.8	25.0	28.0	31.0	34.0	37.0	40.0	44.0	48.0	52.0	58.0	64.0	0.02
BZV90- CXXX		<u>.</u>	22	24	27	30	33	36	39	43	47	51	56	62	68	75

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Voltage regulator diodes

BZV90 series

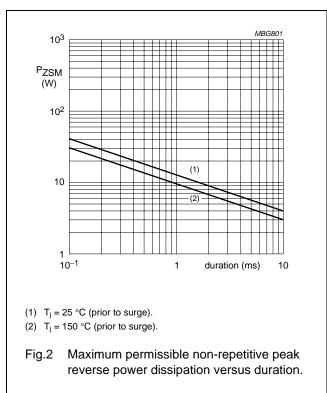
THERMAL CHARACTERISTICS

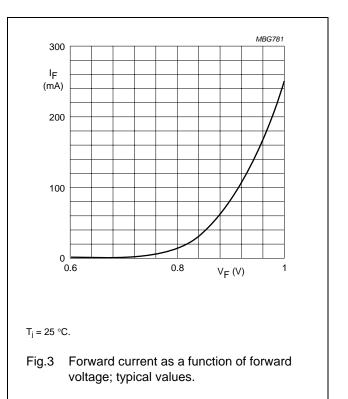
SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	lead length max.; note 1	83.3	K/W

Note

1. Device mounted on an FR4 double-sided copper-clad printed circuit-board; copper area = 2 cm².

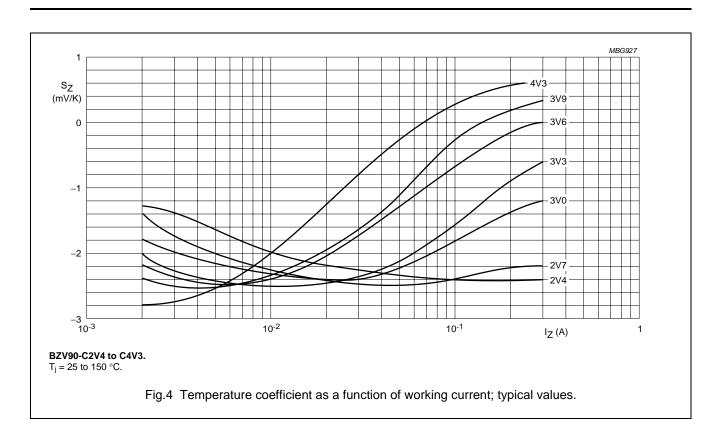
GRAPHICAL DATA

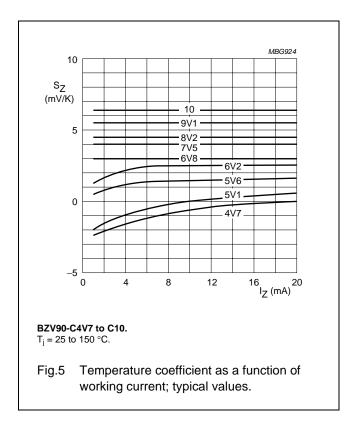




BZV90 series

BZV90 series

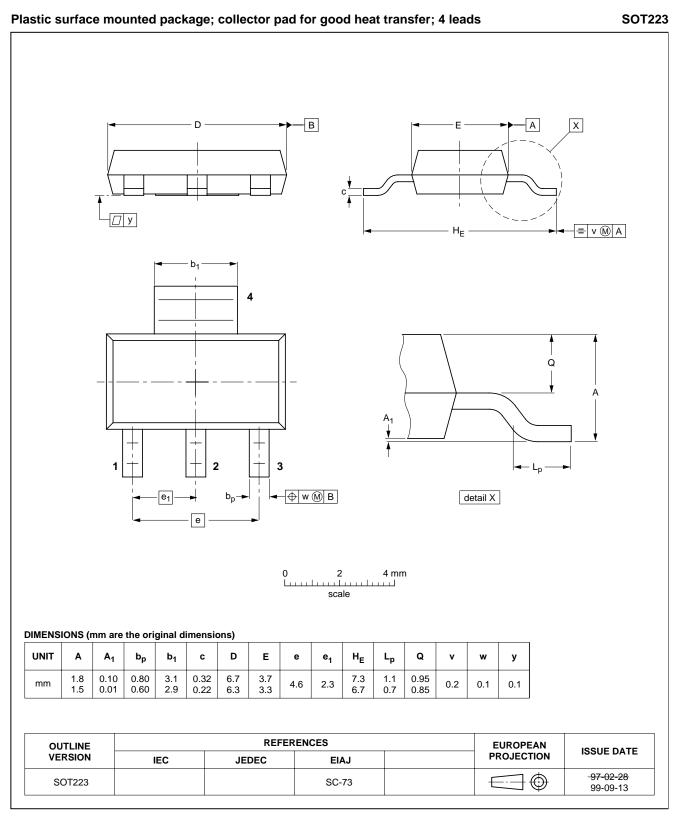




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BZV90 series

PACKAGE OUTLINE



BZV90 series

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

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Contact information

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